

INTERFACE™

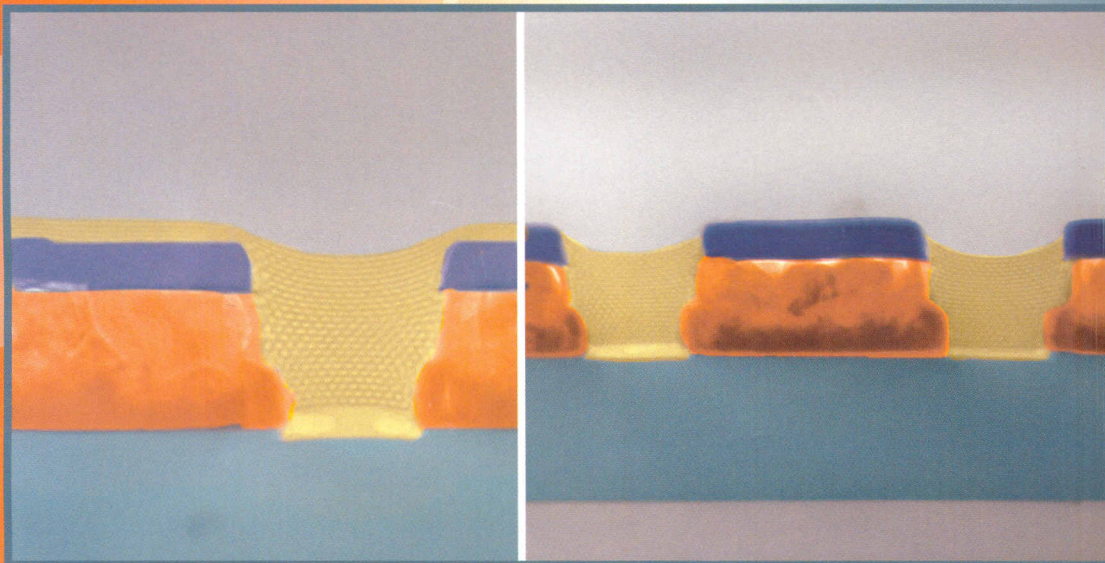
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An example of aligned mesopores in intra-metal channels as Ultra Low- k dielectrics: See article starting on page 44.

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